VS-U5FH120FA60





FRED Pt[®] Gen 5 Ultrafast Rectifier Diode, 600 V, 120 A

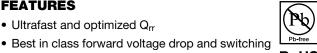


PRIMARY CHARACTERISTICS								
V _R	600 V							
V _F (typical) at 60 A, per diode	1.36 V							
t _{rr} (typical) at 60 A, per diode	67 ns							
$I_{F(DC)}$ per module at $T_C = 115 \text{ °C}$	120 A							
Туре	Modules - diode, FRED Pt [®]							
Package	SOT-227							
Circuit configuration	Two separate diodes, parallel pin-out							

FEATURES

losses trade off

Ultrafast and optimized Q_{rr}



- RoHS COMPLIANT
- · Optimized for high speed operation
- 175 °C maximum operating junction temperature
- · Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- Designed and gualified for industrial level
- UL approved file E78996
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, the VS-U5FH120FA60 is the right choice for high frequency converters, both soft switched / resonant. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters, and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Cathode to anode voltage	V _R		600	V				
Continuous forward current per diode	I _F	T _C = 115 °C	60	^				
Single pulse forward current per diode	I _{FSM}	T _J = 25 °C	485	A				
Maximum power dissipation per module	PD	T _C = 115 °C	171	W				
RMS isolation voltage	VISOL	Any terminal to case, t = 1 min	2500	V				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	600	-	-			
Forward voltage	V _{FM}	I _F = 60 A	-	1.36	1.7	V		
		I _F = 60 A, T _J = 150 °C	-	1.14	-			
		V _R = 600 V	-	0.3	40			
Reverse leakage current	I _{RM}	$T_{\rm J} = 125 \ ^{\circ}\text{C}, \ V_{\rm R} = 600 \ \text{V}$	-	21	-	μA		
		T _J = 150 °C, V _R = 600 V	-	90	-			

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Boyaraa raadyany tima	+	$T_J = 25 \ ^\circ C$		-	67	-		
Reverse recovery time	t _{rr}	T _J = 125 °C	I _F = 60 A, di _F /dt = 1000 A/μs, V _R = 400 V	-	88	-	ns	
Dook rocovery ourrent		T _J = 25 °C		-	19	-	A	
Peak recovery current	I _{RRM}	T _J = 125 °C		-	37	-		
Boyaraa raadyany aharga	Q _{rr}	T _J = 25 °C		-	0.6	-		
Reverse recovery charge		T _J = 125 °C		-	2.2	-	μC	
Junction capacitance	CT	V _R = 600 V, f =	= 1 MHz	-	46.2	-	pF	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Thermal resistance junction to case, per diode			-	-	0.70			
Thermal resistance junction to case, per module	R _{thJC}		-	-	0.35	°C/W		
Thermal resistance case to heatsink, per module	R _{thCS}	Flat, greased surface	-	0.05	-			
Weight			-	30	-	g		
		Torque per diode	-	-	1.1 (9.7)	Nm (lbf.in)		
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)		
Case style				SO	Г-227			



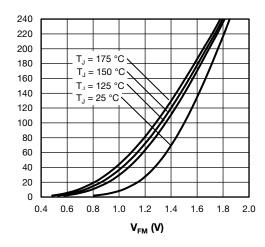


Fig. 1 - Typical Forward Voltage Drop Characteristics

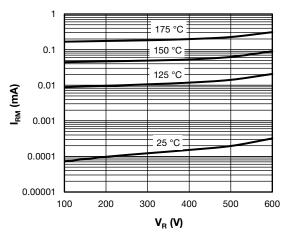


Fig. 2 - Typical Values of Reverse Current



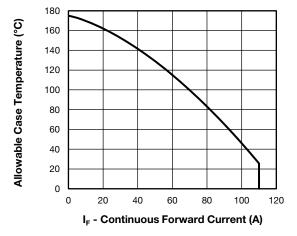


Fig. 3 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Diode)

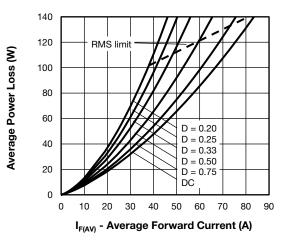


Fig. 4 - Average Power Loss vs. Average Forward Current

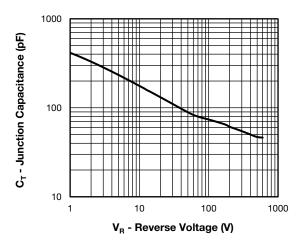


Fig. 5 - Typical Junction Capacitance vs. Reverse Voltage

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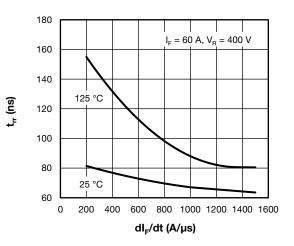


Fig. 6 - Diode Reverse Recovery Time vs. dl_Fdt

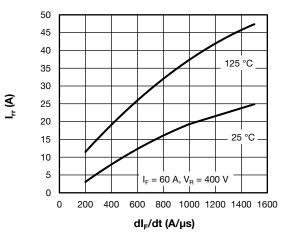


Fig. 7 - Diode Reverse Recovery Current vs. dl_Fdt

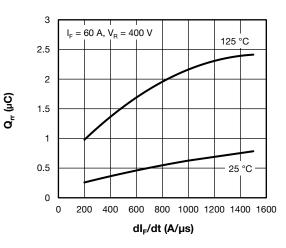


Fig. 8 - Diode Reverse Recovery Charge vs. dl_Fdt

Revision: 19-May-2022

3

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VS-U5FH120FA60 ISHAY www.vishay.com **Vishay Semiconductors** 1 Z_{thJC} - Thermal Impedance Junction to Case (°C/W) 0.50 0.1 0.20 0.10 0.05 ++++ ╫ 0.02 0.01 DC

0.001

н

VS- U5F

t₁ - Rectangular Pulse Duration (s) Fig. 9 - Maximum Thermal Impedance Junction to Case

120

F

0.01

0.1

Α

60

1

ORDERING INFORMATION TABLE

Device code

0.0001

0.01 0.00001

1	2	3	4	5	6	7	-			
1 - 2 - 3 -	U5F H =	= Gen Ultrafa	niconduo 5 FRED st FRED	Pt [®] far Pt [®] dic	nily ode					
4 · 5 ·			ing per r configura		•		odes, par	allel pin-c	out)	
6 - 7 -		•	dicator (ing (60 =			dard ins	ulated b	ase)		
N										

CIRCUIT CONFIGURATION								
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING						
Two separate diodes, parallel pin-out	F	Lead Assignment						

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95423					
Packaging information	www.vishay.com/doc?95425					

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10

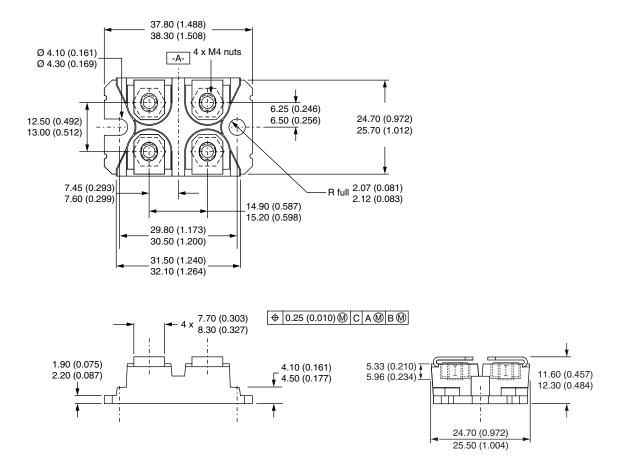


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SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

• Controlling dimension: millimeter



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